IGBT MODULE (S series)
1400V / 25A / PIM

■ Features

■ Applications

- Inverter for Motoe Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply

■ Maximum ratings and characteristics

● **Absolute maximum ratings (Tc=25°C unless without specified)**

Item		Symbol	Condition		Rating	Unit
Inverter	Collector-Emitter voltage	V_{CES}			1400	V
	Gate-Emitter voltage	V_{GES}			±20	V
	Collector current	I_C	Continuous	Tc=25°C	35	A
				Tc=75°C	25	
		I_{CP}	1ms	Tc=25°C	70	A
				Tc=75°C	50	
		$-I_C$			25	A
	Collector power disspation	P_C	1 device		180	W
Brake	Collector-Emitter voltage	V_{CES}			1400	V
	Gate-Emitter voltage	V_{GES}			±20	V
	Collector current	I_C	Continuous	Tc=25°C	25	A
				Tc=75°C	15	
		I_{CP}	1ms	Tc=25°C	50	A
				Tc=75°C	30	
	Collector power disspation	P_C	1 device		110	W
	Repetitive peak reverse voltage	V_{RRM}			1400	V
Converter	Repetitive peak reverse voltage	V_{RRM}			1600	V
	Average output current	I_O	50Hz/60Hz sine wave		25	A
	Surge current (Non-Repetitive)	I_{FSM}	Tj=150°C, 10ms		260	A
	I^2t (Non-Repetitive)	I^2t	half sine wave		338	A^2s
Operating junction temperature		T_j			+150	°C
Storage temperature		T_{stg}			-40 to +125	°C
Isolation voltage	between terminal and copper base *2	V_{iso}	AC : 1 minute		AC 2500	V
	between thermistor and others *3				AC 2500	
Mounting screw torque					3.5 *1	N·m

*1 Recommendable value : 2.5 to 3.5 N·m (M5)

*2 All terminals should be connected together when isolation test will be done.

*3 Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 24 should be connected together and shorted to copper base.

● Electrical characteristics (Tj=25°C unless otherwise specified)

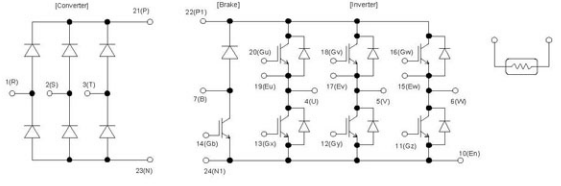
Item		Symbol	Condition		Characteristics Min.	Typ.	Max.	Unit
Inverter	Zero gate voltage collector current	I_{CES}	V_{CE}=1400V, V_{GE}=0V				1.0	mA
	Gate-Emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=±20V				0.2	μA
	Gate-Emitter threshold voltage	$V_{GE(th)}$	V_{CE}=20V, I_C=25mA		5.5	7.2	8.5	V
	Collector-Emitter saturation voltage	$V_{CE(sat)}$	V_{GE}=15V, Ic=25A	chip		2.2		V
				terminal		2.3	2.7	
	Input capacitance	C_{ies}	V_{GE}=0V, V_{CE}=10V, f=1MHz			3000		pF
	Turn-on time	t_{on}	V_{CC}=800V			0.35	1.2	μs
		t_r	I_C=25A			0.25	0.6	
		$t_{r(i)}$	V_{GE}=±15V			0.1		
	Turn-off	t_{off}	R_G=51Ω			0.45	1.0	
		t_f				0.08	0.3	
	Forward on voltage	V_F	I_F=25A	chip		2.4		V
				terminal		2.5	3.3	
	Reverse recovery time of FRD	t_{rr}	I_F=25A				0.35	μs
Brake	Zero gate voltage collector current	I_{CES}	V_{CES}=1400V, V_{GE}=0V				1.0	mA
	Gate-Emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=±20V				0.2	μA
	Collector-Emitter saturation voltage	$V_{CE(sat)}$	I_C=15A, V_{GE}=15V	chip		2.2		V
				terminal		2.3	2.7	
	Turn-on time	t_{on}	V_{CC}=800V			0.35	1.2	μs
		t_r	I_C=15A			0.25	0.6	
	Turn-off time	t_{off}	V_{GE}=±15V			0.45	1.0	
		t_f	R_G=82 Ω			0.08	0.3	
	Reverse current	I_{RRM}	V_R=1400V				1.0	mA
Converter	Forward on voltage	V_{FM}	I_F=25A	chip		1.1		V
				terminal		1.2	1.5	
	Reverse current	I_{RRM}	V_R=1600V				1.0	mA
	Resistance	R	T=25°C			5000		Ω
			T=100°C		465	495	520	
	B value	B	T=25/50°C		3305	3375	3450	K

● Thermal resistance Characteristics

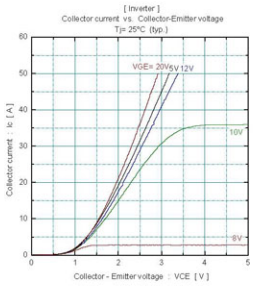
Item	Symbol	Condition	Characteristics Min.	Typ.	Max.	Unit
Thermal resistance (1 device)	Rth(j-c)	Inverter IGBT			0.69	°C/W
		Inverter FWD			1.30	
		Brake IGBT			1.14	
		Converter Diode			0.90	
Contact thermal resistance *	Rth(c-f)	With thermal compound		0.05		

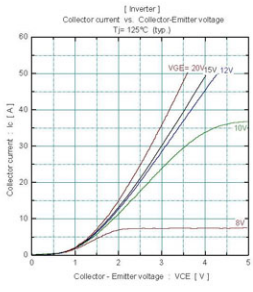
* This is the value which is defined mounting on the additional cooling fin with thermal compound

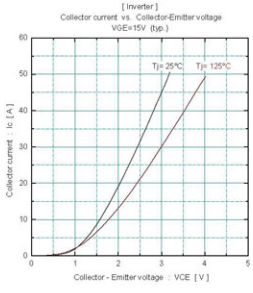
■ Equivalent Circuit Schematic

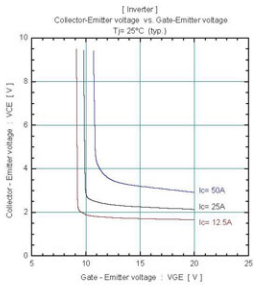


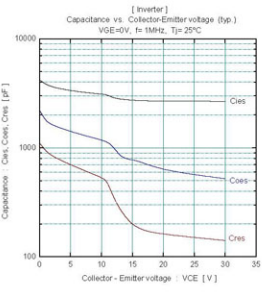
■ Characteristics (Representative)

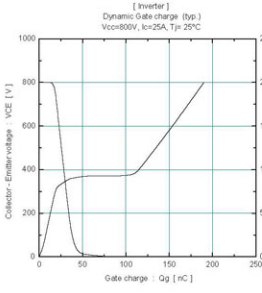


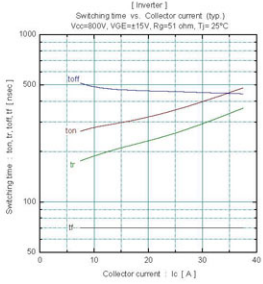


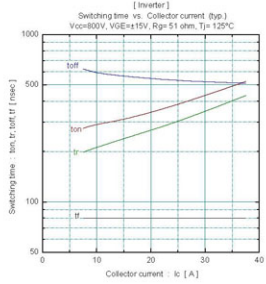


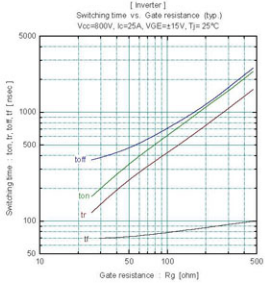


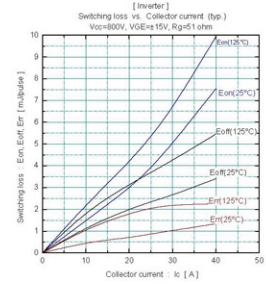


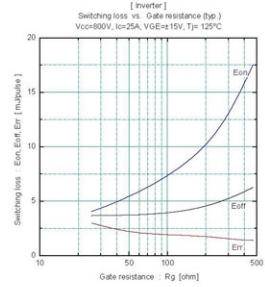


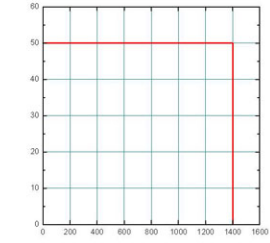

[Inverter]
Switching time vs. Collector current (typ.)
Vcc=800V, VGE=±15V, Rg=51 ohm, Tj= 25°C
Switching time : ton, tr, toff, tf [nsec]
Collector current : Ic [A]
toff
ton
tr
tf


[Inverter]
Switching time vs. Collector current (typ.)
Vcc=800V, VGE=±15V, Rg= 51 ohm, Tj= 125°C
Switching time : ton, tr, toff, tf [nsec]
Collector current : [A]
toff
ton
tr
tf

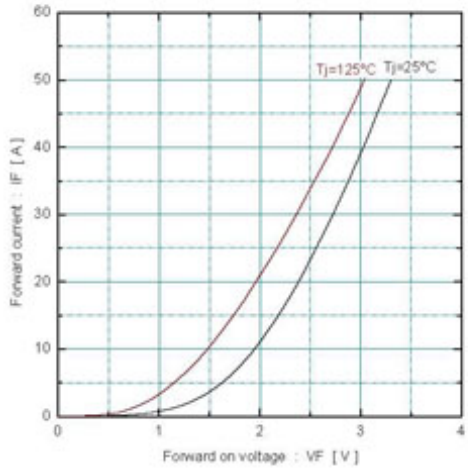

[Inverter]
Switching time vs. Gate resistance (typ.)
Vcc=800V, Ic=25A, VGE=±15V, Tj= 25°C
Switching time : ton, tr, toff, tf [nsec]
Gate resistance : Rg [ohm]
toff
ton
tr
tf


[Inverter]
Switching loss vs. Collector current (typ.)
Vcc=800V, VGE=±15V, Rg=51 ohm
Switching loss : Eon, Eoff, Err [mJ/pulse]
Collector current : Ic [A]
Eon(125°C)
Eon(25°C)
Eoff(125°C)
Eoff(25°C)
Err(125°C)
Err(25°C)

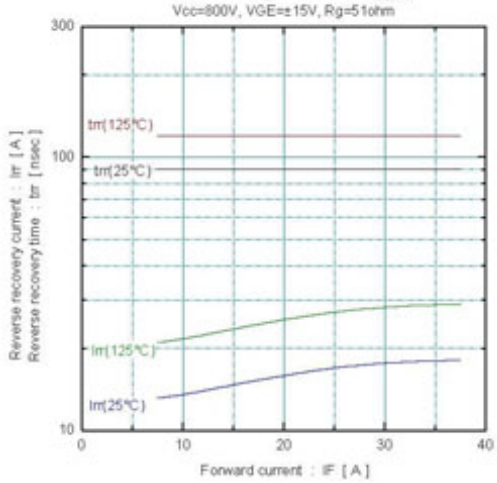

[Inverter]
Switching loss vs. Gate resistance (typ.)
Vcc=800V, Ic=25A, VGE=±15V, Tj= 125°C
Switching loss : Eon, Eoff, Err [mJ/pulse]
Gate resistance : Rg [ohm]
Eon
Eoff
Err



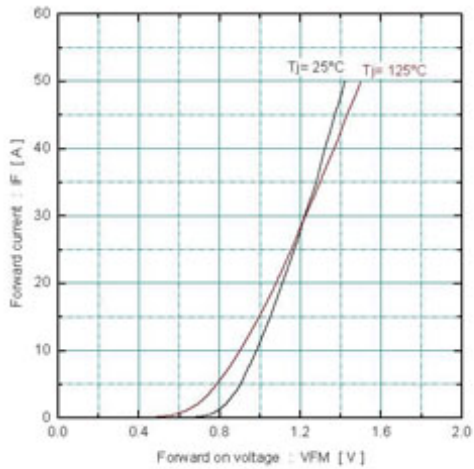
[Inverter]
Forward current vs. Forward on voltage (typ.)



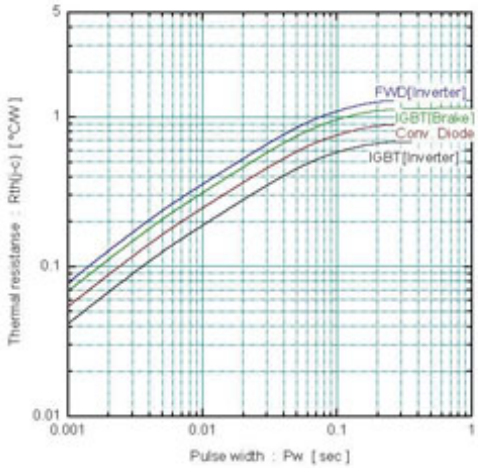
[Inverter]
Reverse recovery characteristics (typ.)
Vcc=800V, VGE=±15V, Rg=51ohm

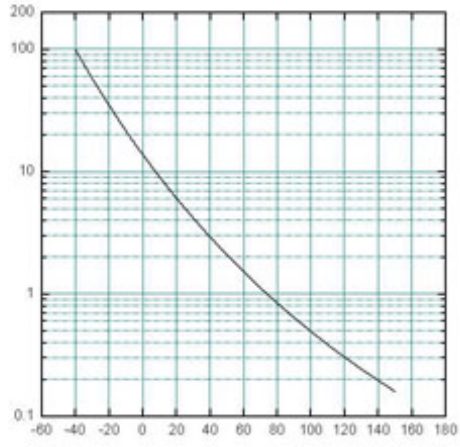


[Converter]
Forward current vs. Forward on voltage (typ.)

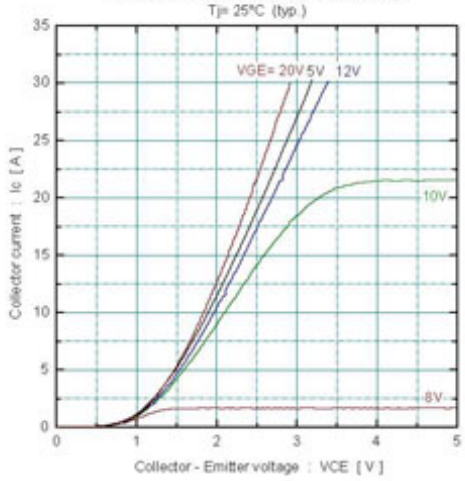


Transient thermal resistance

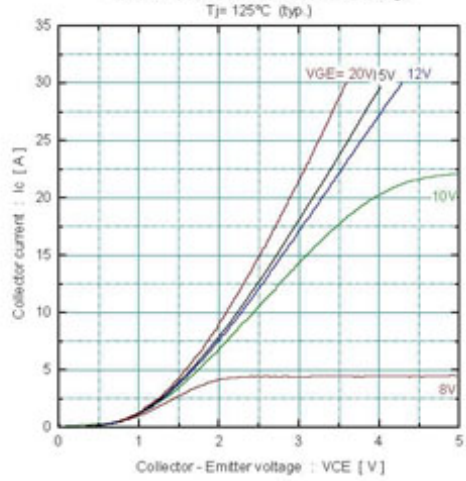




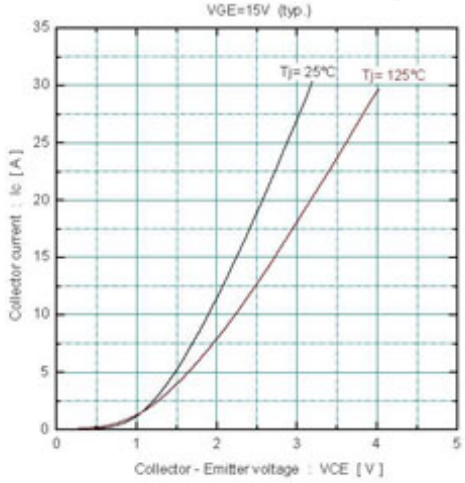
[Brake]
Collector current vs. Collector-Emitter voltage
Tj= 25°C (typ.)



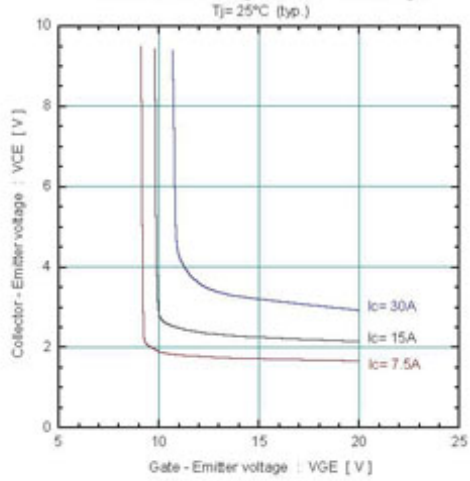
[Brake]
Collector current vs. Collector-Emitter voltage
Tj= 125°C (typ.)



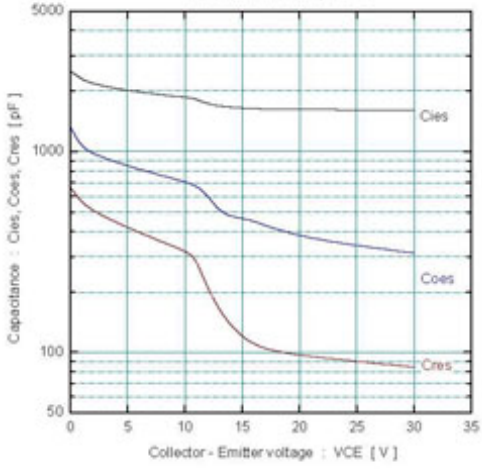
[Brake]
Collector current vs. Collector-Emitter voltage
VGE=15V (typ.)



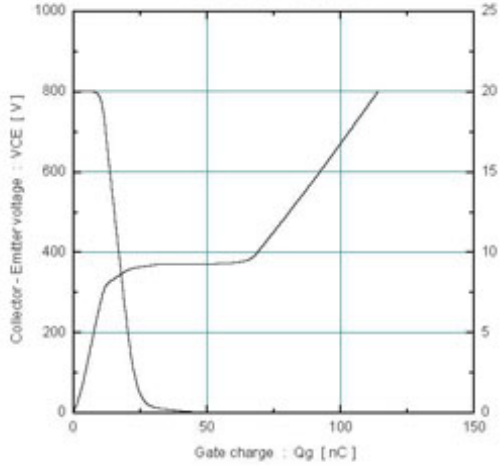
[Brake]
Collector-Emitter voltage vs. Gate-Emitter voltage
Tj= 25°C (typ.)



[Brake]
Capacitance vs. Collector-Emitter voltage (typ.)
VGE=0V, f= 1MHz, Tj= 25°C



[Brake]
Dynamic Gate charge (typ.)
Vcc=800V, Ic=15A, Tj= 25°C



■ Outline Drawings, mm